

HAT2187WP

Silicon N Channel Power MOS FET
Power Switching

REJ03G0535-0500

Rev.5.00

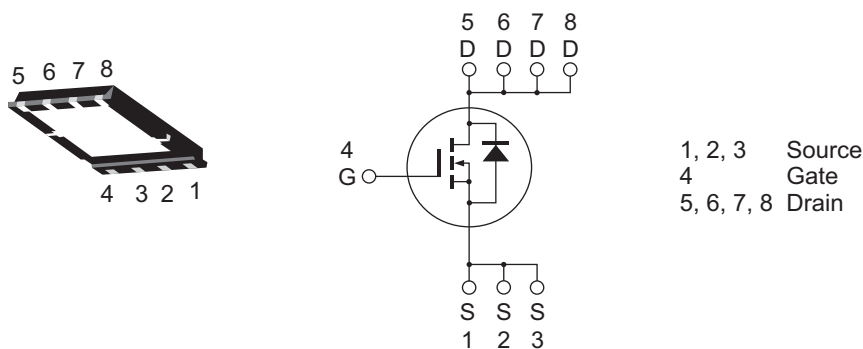
Sep.02,2005

Features

- Low on-resistance
- Low drive current
- High density mounting

Outline

RENESAS Package code: PWSN0008DA-A
(Package name: WPAK)



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	200	V
Gate to source voltage	V_{GSS}	± 30	V
Drain current	I_D	17	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	34	A
Body-drain diode reverse drain current	I_{DR}	17	A
Body-drain diode reverse drain peak current	$I_{DR(pulse)}$ ^{Note1}	34	A
Avalanche current	I_{AP} ^{Note3}	17	A
Avalanche energy	E_{AR} ^{Note3}	19.2	mJ
Channel dissipation	P_{ch} ^{Note2}	30	W
Channel to case thermal impedance	θ_{ch-c}	4.17	°C/W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$

2. Value at $T_c = 25^\circ C$

3. $STch = 25^\circ C$, $T_{ch} \leq 150^\circ C$

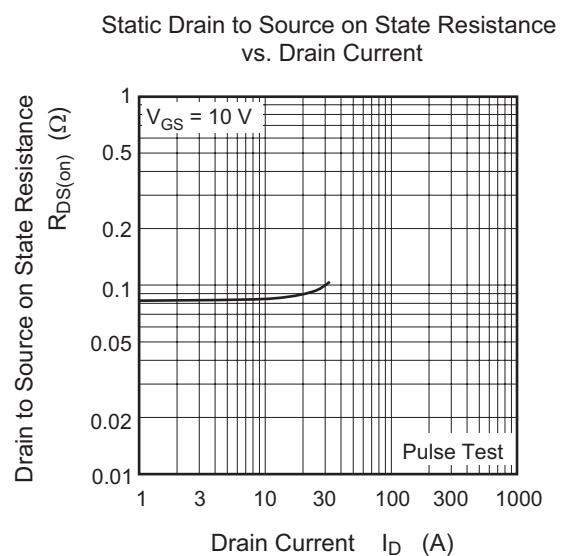
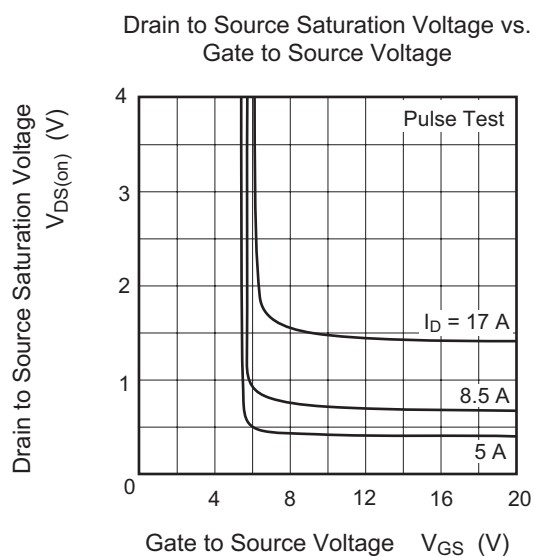
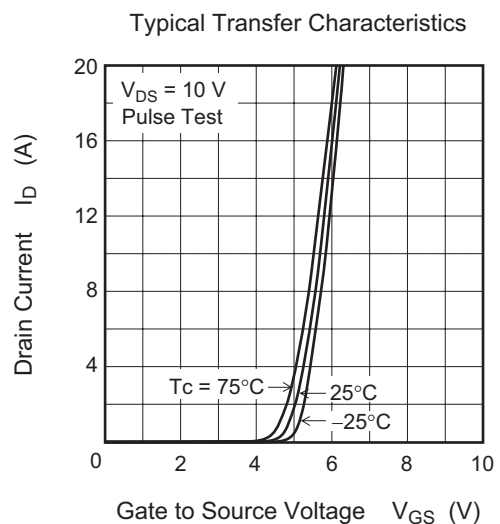
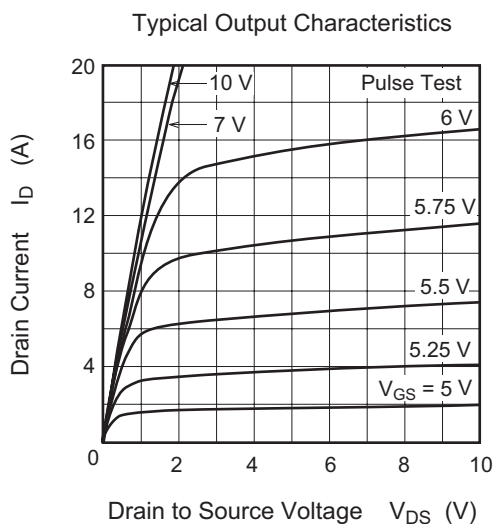
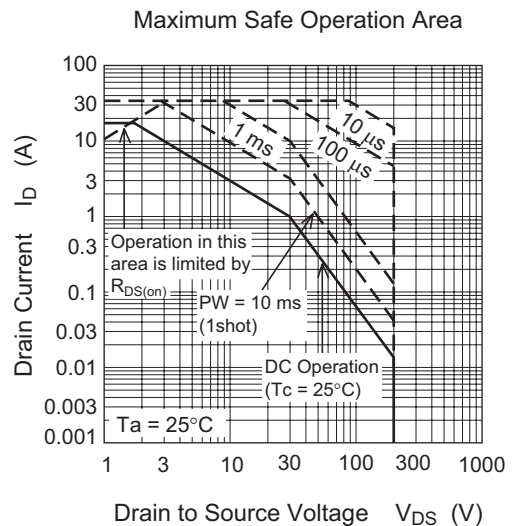
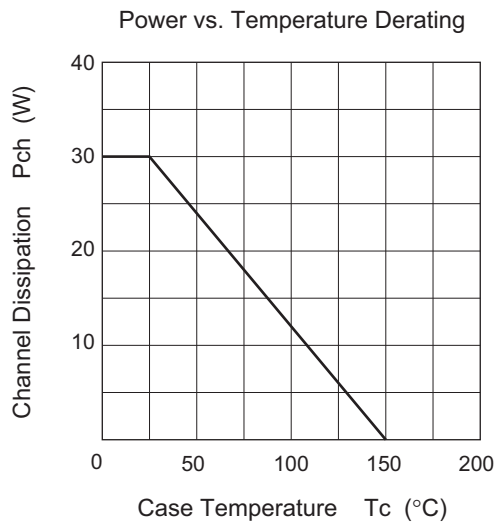
Electrical Characteristics

(Ta = 25°C)

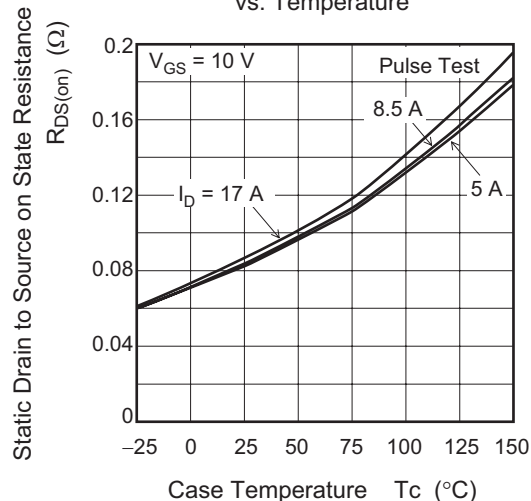
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	200	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 200 \text{ V}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	—	4.5	V	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$
Forward transfer admittance	$ y_{fs} $	8	14	—	S	$I_D = 8.5 \text{ A}$, $V_{DS} = 10 \text{ V}$ ^{Note4}
Static drain to source on state resistance	$R_{DS(on)}$	—	0.084	0.094	Ω	$I_D = 8.5 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	1200	—	pF	$V_{DS} = 25 \text{ V}$ $V_{GS} = 0$ $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	220	—	pF	
Reverse transfer capacitance	C_{rss}	—	19	—	pF	
Turn-on delay time	$t_{d(on)}$	—	31	—	ns	$I_D = 8.5 \text{ A}$ $V_{GS} = 10 \text{ V}$ $R_L = 11.8 \Omega$ $R_g = 10 \Omega$
Rise time	t_r	—	37	—	ns	
Turn-off delay time	$t_{d(off)}$	—	69	—	ns	
Fall time	t_f	—	8	—	ns	
Total gate charge	Q_g	—	26	—	nC	$V_{DD} = 160 \text{ V}$ $V_{GS} = 10 \text{ V}$ $I_D = 17 \text{ A}$
Gate to Source charge	Q_{gs}	—	7	—	nC	
Gate to drain charge	Q_{gd}	—	10	—	nC	
Body-drain diode forward voltage	V_{DF}	—	0.9	1.4	V	$I_F = 17 \text{ A}$, $V_{GS} = 0$ ^{Note4}
Body-drain diode reverse recovery time	t_{rr}	—	130	—	ns	$I_F = 17 \text{ A}$, $V_{GS} = 0$ $diF/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

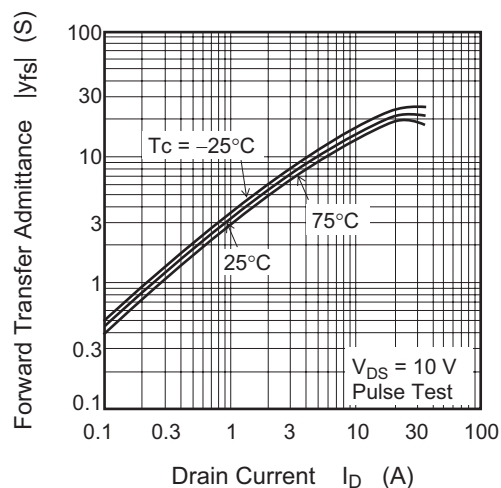
Main Characteristics



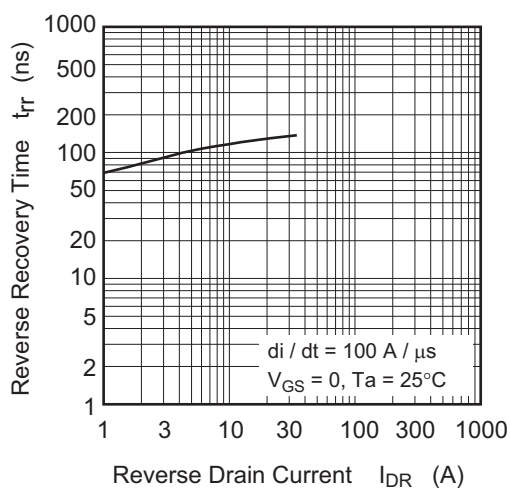
Static Drain to Source on State Resistance vs. Temperature



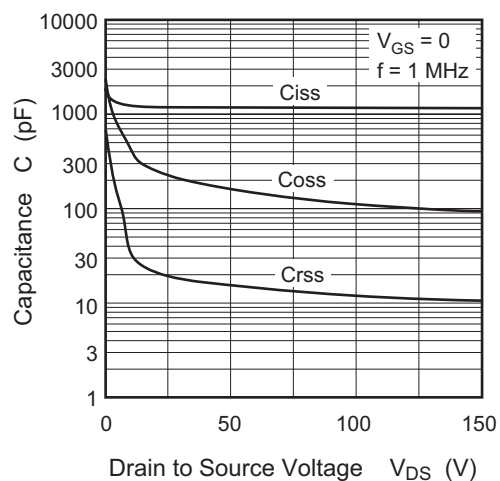
Forward Transfer Admittance vs. Drain Current



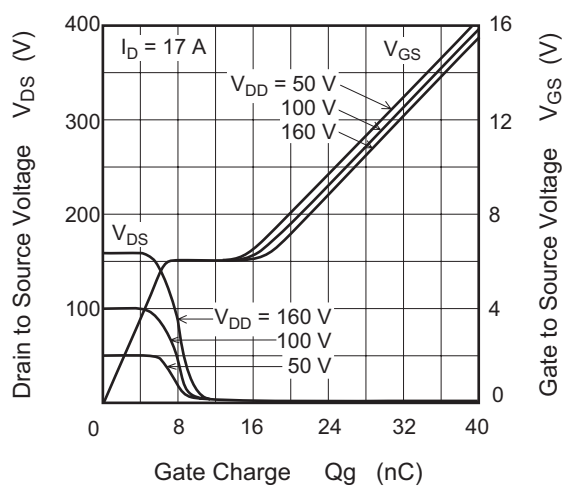
Body-Drain Diode Reverse Recovery Time



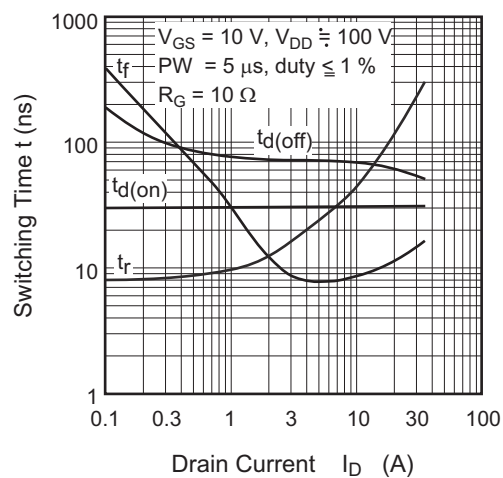
Typical Capacitance vs. Drain to Source Voltage

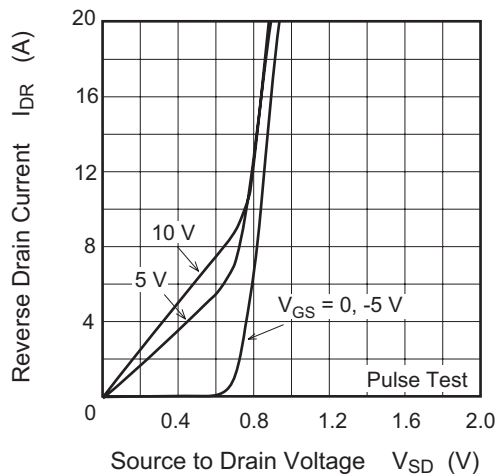
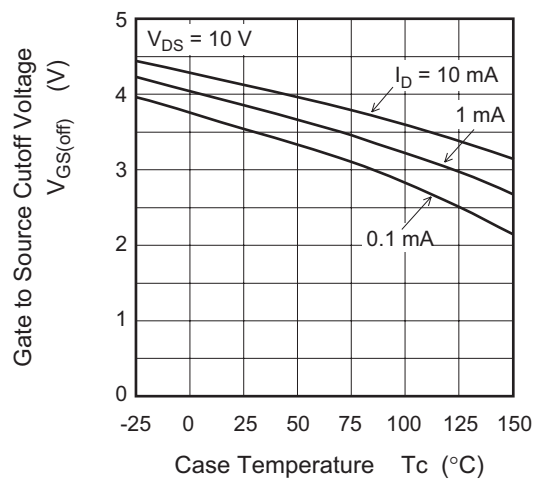


Dynamic Input Characteristics

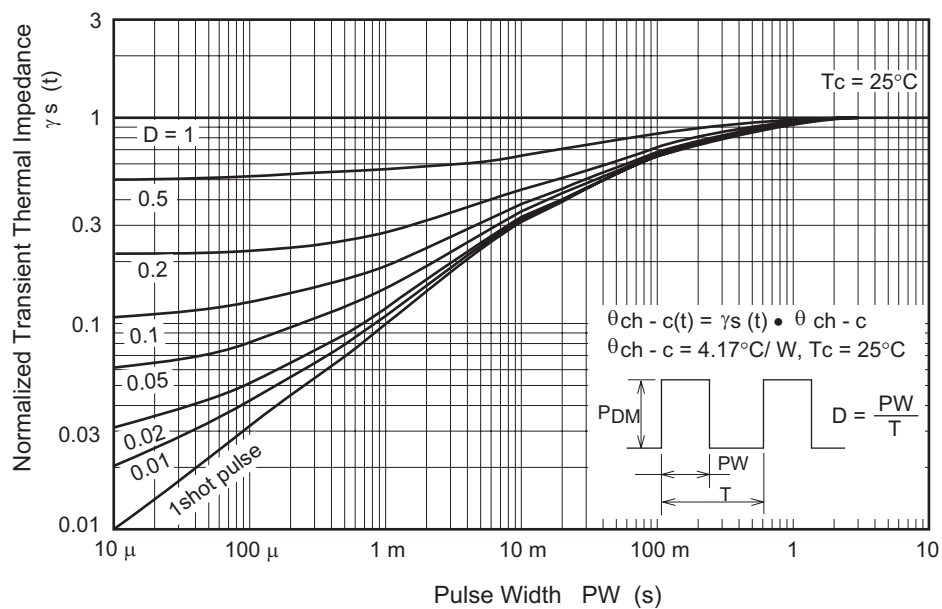


Switching Characteristics

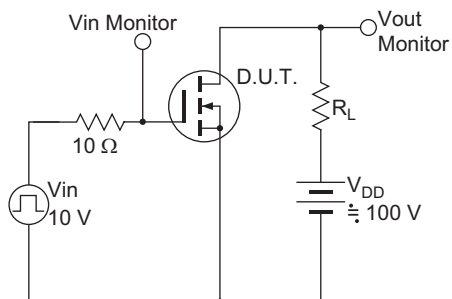


Reverse Drain Current vs.
Source to Drain VoltageGate to Source Cutoff Voltage
vs. Case Temperature

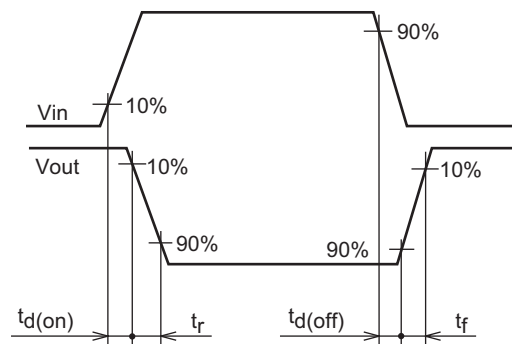
Normalized Transient Thermal Impedance vs. Pulse Width



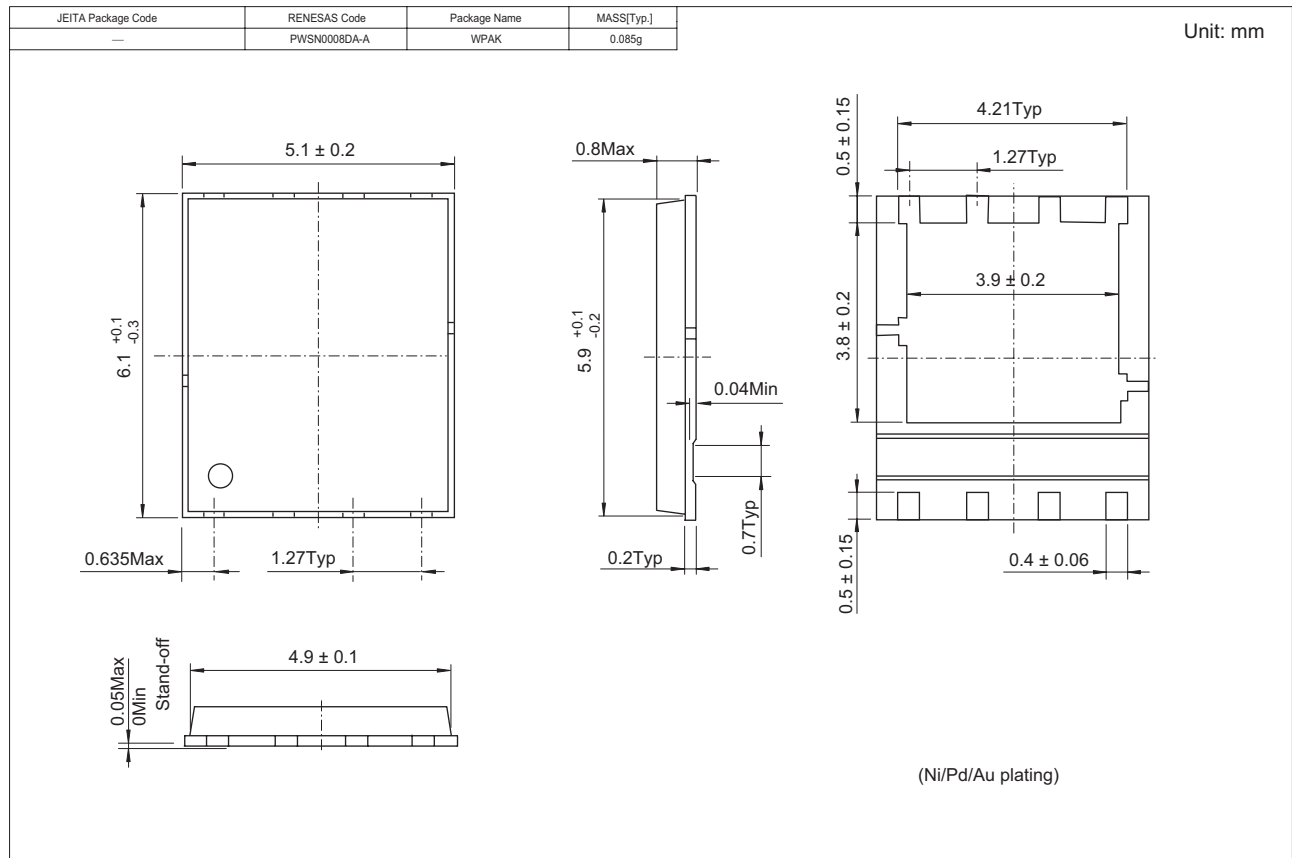
Switching Time Test Circuit



Waveform



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAT2187WP-EL-E	2500 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510